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Fairchild Semiconductor
NDB4050

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FAIRCHILD SEMICONDUCTOR TM

July 1996

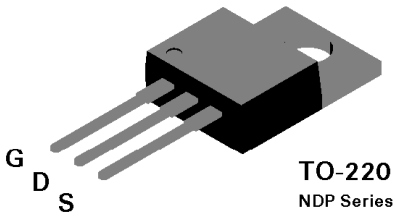
# NDP4050 / NDB4050
# N-Channel Enhancement Mode Field Effect Transistor

## General Description

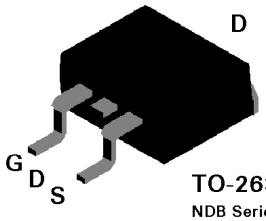
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

## Features

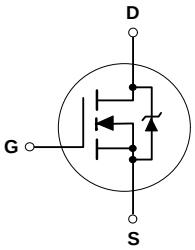
- 15A, 50V. $R_{DS(ON)}$ = 0.10Ω @ $V_{GS}$=10V.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low $R_{DS(ON)}$.
- TO-220 and TO-263 ($D^2$PAK) package for both through hole and surface mount applications.




TO-220
NDP Series




TO-263AB
NDB Series




## Absolute Maximum Ratings

$T_C$ = 25°C unless otherwise noted

| Symbol | Parameter | NDP4050 | NDB4050 | Units |
|---|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | 50 | | V |
| $V_{DGR}$ | Drain-Gate Voltage ($R_{GS}$ ≤ 1 MΩ) | 50 | | V |
| $V_{GSS}$ | Gate-Source Voltage - Continuous | ± 20 | | V |
| | - Nonrepetitive ($t_p$ < 50 µs) | ± 40 | | |
| $I_D$ | Drain Current - Continuous | ± 15 | | A |
| | - Pulsed | ± 45 | | |
| $P_D$ | Total Power Dissipation | 50 | | W |
| | Derate above 25°C | 0.33 | | W/°C |
| $T_J$,$T_{STG}$ | Operating and Storage Temperature Range | -65 to 175 | | °C |
| $T_L$ | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 275 | | °C |

## Electrical Characteristics ($T_C$ = 25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **DRAIN-SOURCE AVALANCHE RATINGS** (Note 1) | | | | | | |
| $W_{DSS}$ | Single Pulse Drain-Source Avalanche Energy | $V_{DD}$ = 25 V, $I_D$ = 15 A | | | 40 | mJ |
| $I_{AR}$ | Maximum Drain-Source Avalanche Current | | | | 15 | A |
| **OFF CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 50 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 50 V, $V_{GS}$ = 0 V | | | 250 | µA |
| | | $T_J$ = 125°C | | | 1 | mA |
| $I_{GSSF}$ | Gate - Body Leakage, Forward | $V_{GS}$ = 20 V, $V_{DS}$ = 0 V | | | 100 | nA |
| $I_{GSSR}$ | Gate - Body Leakage, Reverse | $V_{GS}$ = -20 V, $V_{DS}$ = 0 V | | | -100 | nA |
| **ON CHARACTERISTICS** (Note 1) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 2 | 3 | 4 | V |
| | | $T_J$ = 125°C | 1.4 | 2.4 | 3.6 | |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}$ = 10 V, $I_D$ = 7.5 A | | 0.078 | 0.1 | Ω |
| | | $T_J$ = 125°C | | 0.12 | 0.165 | |
| $I_{D(on)}$ | On-State Drain Current | $V_{GS}$ = 10 V, $V_{DS}$ = 10 V | 15 | | | A |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 10 V, $I_D$ = 7.5 A | 3 | 5.7 | | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 25, $V_{GS}$ = 0 V, f = 1.0 MHz | | 370 | 450 | pF |
| $C_{oss}$ | Output Capacitance | | | 165 | 200 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 50 | 100 | pF |
| **SWITCHING CHARACTERISTICS** (Note 1) | | | | | | |
| $t_{D(on)}$ | Turn - On Delay Time | $V_{DD}$ = 30 V, $I_D$ = 15 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 25 Ω | | 8 | 20 | ns |
| $t_r$ | Turn - On Rise Time | | | 70 | 100 | ns |
| $t_{D(off)}$ | Turn - Off Delay Time | | | 18 | 30 | ns |
| $t_f$ | Turn - Off Fall Time | | | 37 | 50 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = 48 V, $I_D$ = 15 A, $V_{GS}$ = 10 V | | 12.7 | 17 | nC |
| $Q_{gs}$ | Gate-Source Charge | | | 3.2 | | nC |
| $Q_{gd}$ | Gate-Drain Charge | | | 7 | | nC |

## Electrical Characteristics ($T_C$ = 25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS** | | | | | | |
| $I_S$ | Maximum Continuos Drain-Source Diode Forward Current | | | | 15 | A |
| $I_{SM}$ | Maximum Pulsed Drain-Source Diode Forward Current | | | | 45 | A |
| $V_{SD}$ | Source-Drain Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 7.5 A (Note 1) | | 0.95 | 1.3 | V |
| | | $T_J$ = 125°C | | 0.88 | 1.2 | |
| $t_{rr}$ | Reverse Recovery Time | $V_{GS}$ = 0 V, $I_F$ = 15 A, $dI_F/dt$ = 100 A/µs | 25 | 46 | 100 | ns |
| $I_{rr}$ | Reverse Recovery Current | | 1.5 | 3.4 | 7 | A |
| **THERMAL CHARACTERISTICS** | | | | | | |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | | | | 3 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | | | | 62.5 | °C/W |

Note:
1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

## Typical Electrical Characteristics

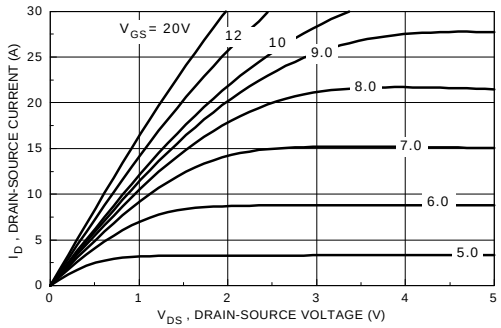



**Figure 1. On-Region Characteristics.**

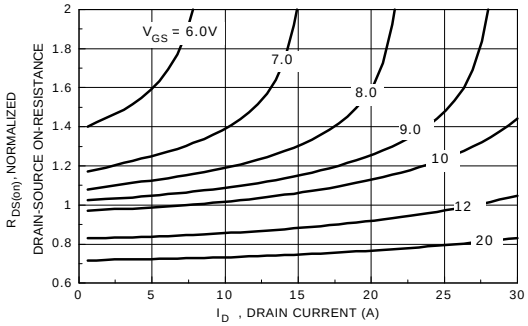



**Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.**

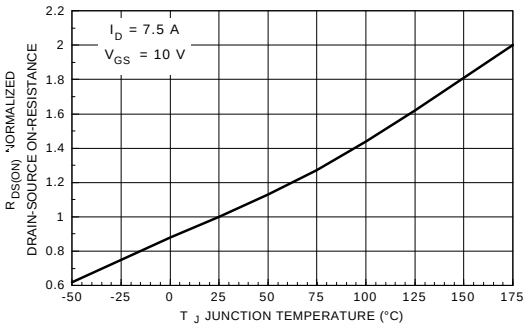



**Figure 3. On-Resistance Variation with Temperature.**

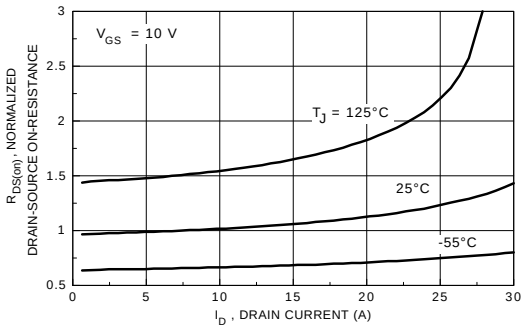



**Figure 4. On-Resistance Variation with Drain Current and Temperature.**

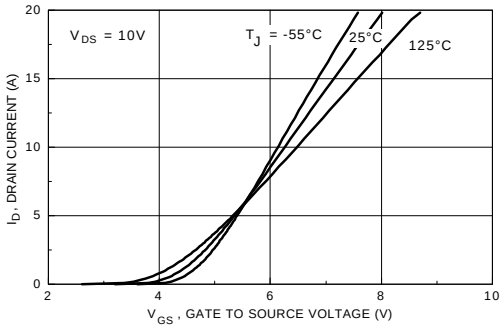



**Figure 5. Drain Current Variation with Gate Voltage and Temperature.**

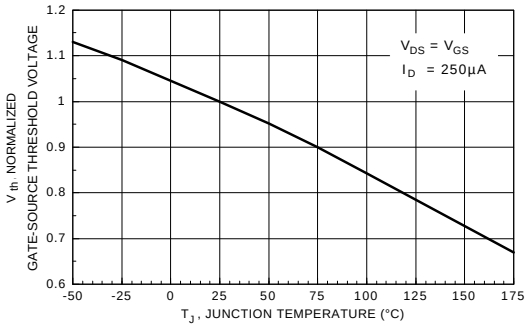



**Figure 6. Gate Threshold Variation with Temperature.**

## Typical Electrical Characteristics (continued)

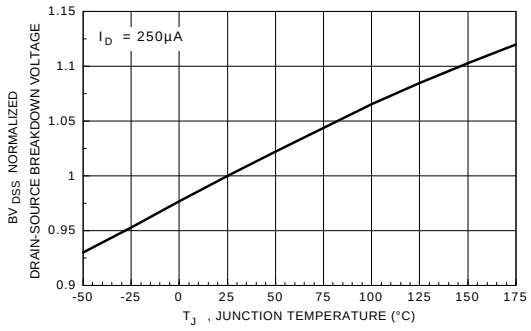



**Figure 7. Breakdown Voltage Variation with Temperature.**

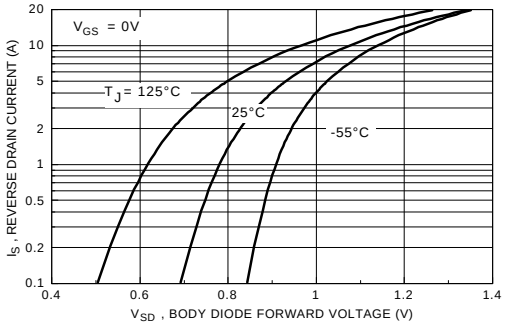



**Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.**

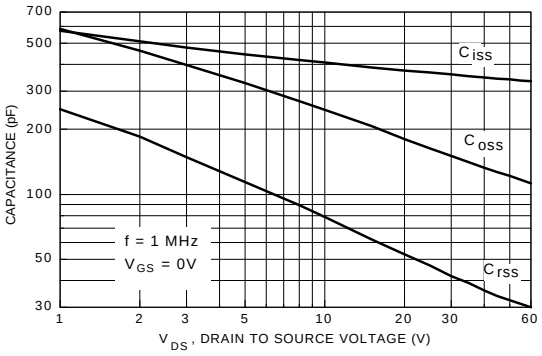



**Figure 9. Capacitance Characteristics.**

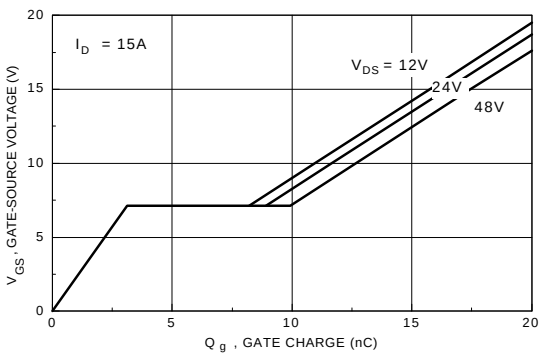



**Figure 10. Gate Charge Characteristics.**

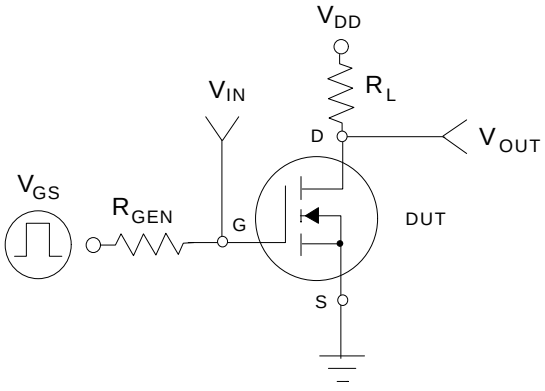



**Figure 11. Switching Test Circuit.**

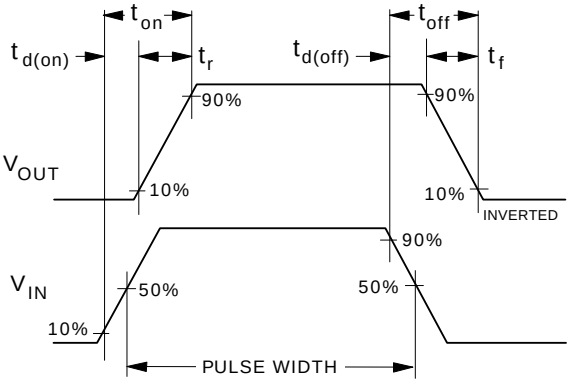



**Figure 12. Switching Waveforms.**

## Typical Electrical Characteristics (continued)

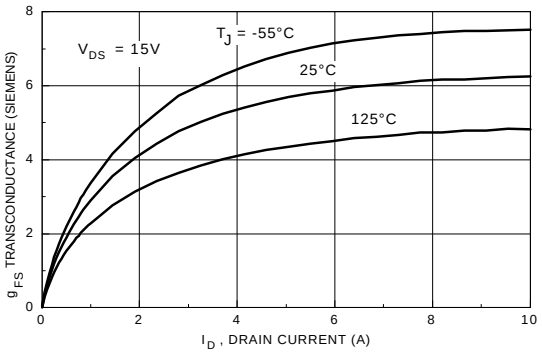



**Figure 13. Transconductance Variation with Drain Current and Temperature.**

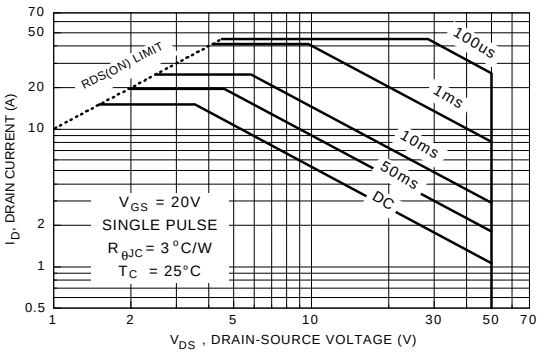



**Figure 14. Maximum Safe Operating Area.**

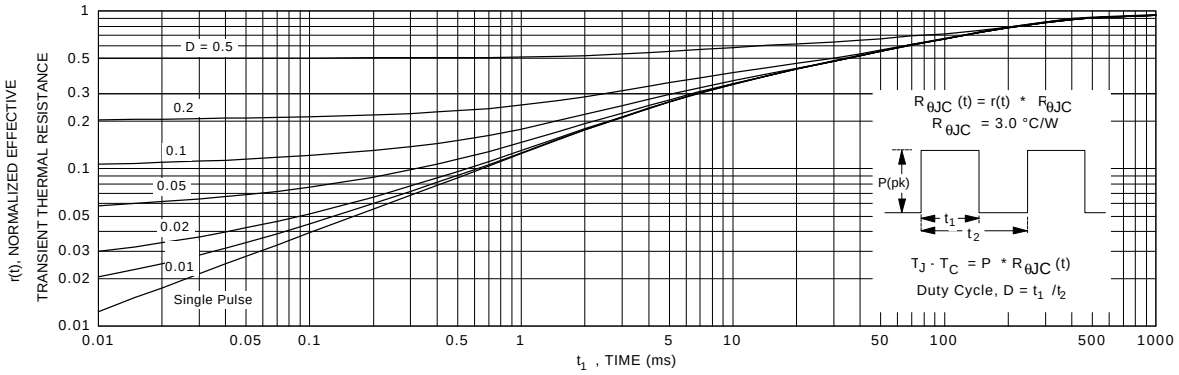



**Figure 15. Transient Thermal Response Curve.**